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HMC358MS8G / 358MS8GE

**MMIC VCO w/ BUFFER
AMPLIFIER, 5.8 - 6.8 GHz**

Typical Applications

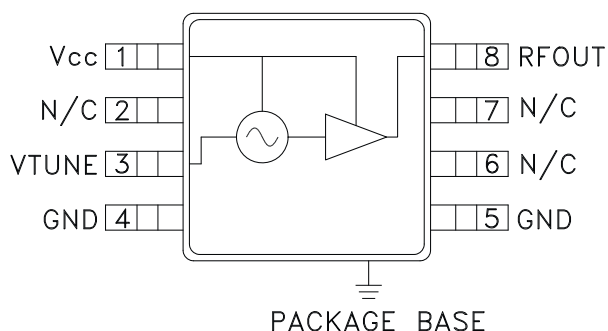
Low noise MMIC VCO w/Buffer Amplifier
for C-Band applications such as:

- UNII & Pt. to Pt. Radios
- 802.11a & HiperLAN WLAN
- VSAT Radios

Features

Pout: +11 dBm
Phase Noise: -110 dBc/Hz @100 KHz
No External Resonator Needed
Single Supply: 3V @ 100 mA
15mm² MSOP8G SMT Package

Functional Diagram



General Description

The HMC358MS8G & HMC358MS8GE are GaAs InGaP Heterojunction Bipolar Transistor (HBT) MMIC VCOs. The HMC358MS8G & HMC358MS8GE integrate resonators, negative resistance devices, varactor diodes, and buffer amplifiers. The VCO's phase noise performance is excellent over temperature, shock, and process due to the oscillator's monolithic structure. Power output is 11 dBm typical from a 3V supply voltage. The voltage controlled oscillator is packaged in a low cost, surface mount 8 lead MSOP package with an exposed base for improved RF and thermal performance.

Electrical Specifications, $T_A = +25^\circ \text{C}$, $V_{CC} = +3\text{V}$

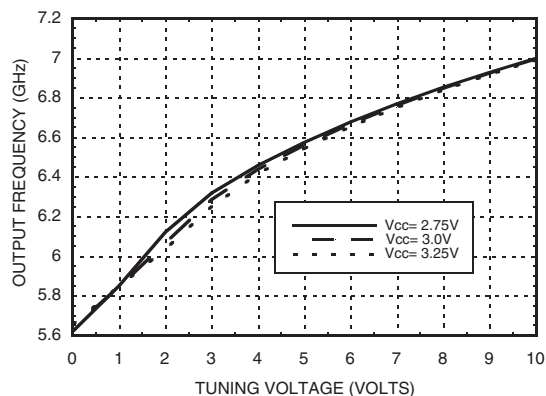
Parameter	Min.	Typ.	Max.	Units
Frequency Range		5.8 - 6.8		GHz
Power Output	8	11		dBm
SSB Phase Noise @ 100 kHz Offset, $V_{tune} = +5\text{V}$ @ RF Output		-110		dBc/Hz
Tune Voltage (V_{tune})	0		10	V
Supply Current (I_{CC})		100		mA
Tune Port Leakage Current ($V_{tune} = 10\text{V}$)			10	μA
Output Return Loss		9		dB
Harmonics				
2nd		-10		dB
3rd		-20		dB
Pulling (into a 2.0:1 VSWR)		10		MHz pp
Pushing @ $V_{tune} = +3\text{V}$		150		MHz/V
Frequency Drift Rate		0.8		MHz/ $^\circ\text{C}$

For price, delivery, and to place orders, please contact Hittite Microwave Corporation:
20 Alpha Road, Chelmsford, MA 01824 Phone: 978-250-3343 Fax: 978-250-3373
Order On-line at www.hittite.com

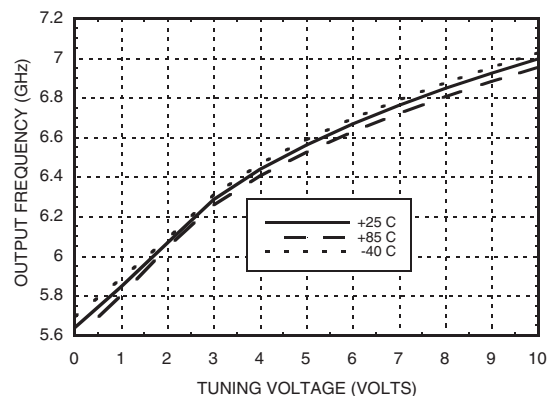
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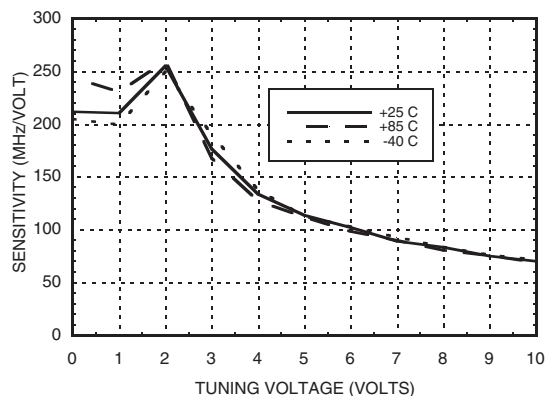
Frequency vs. Tuning Voltage, $T = 25^\circ\text{C}$



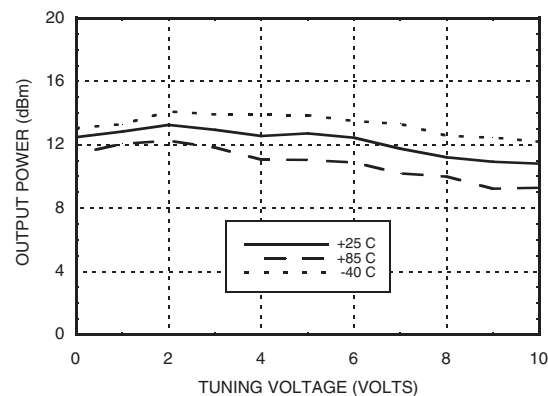
Frequency vs. Tuning Voltage, $V_{cc} = +3\text{V}$



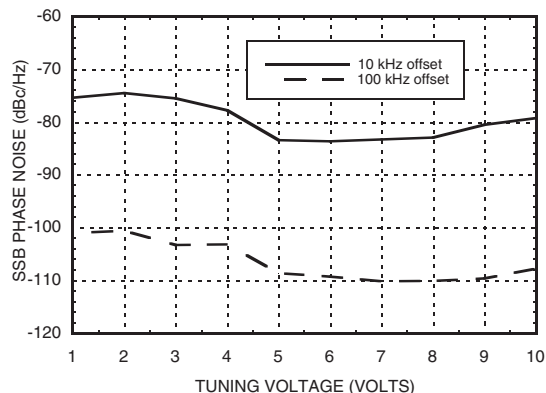
Sensitivity vs. Tuning Voltage, $V_{cc} = +3\text{V}$



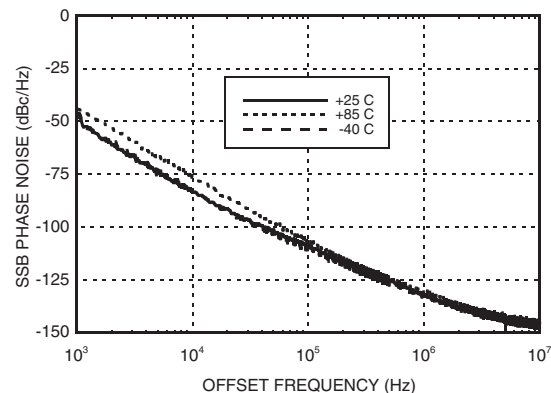
**Output Power vs.
Tuning Voltage, $V_{cc} = +3\text{V}$**



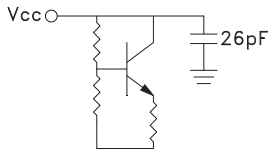
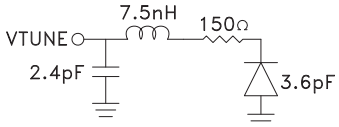

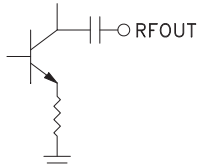
Phase Noise vs. Tuning Voltage



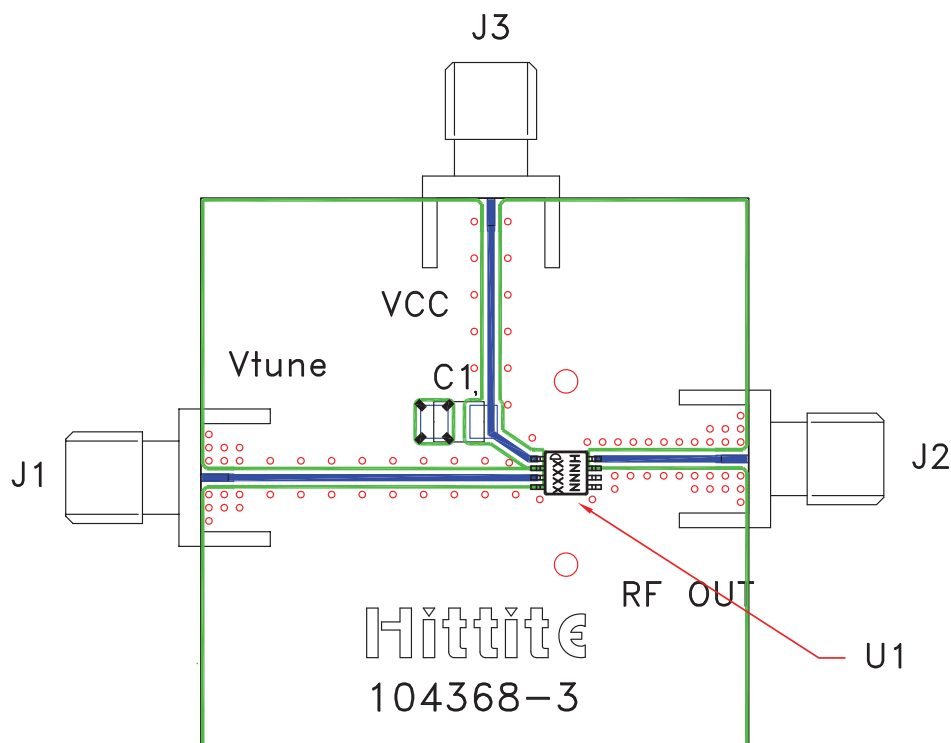
Typical SSB Phase Noise @ $V_{tune} = +5\text{V}$



Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1	Vcc	Supply Voltage Vcc= 3V	
2, 6, 7	N/C	No Connection	
3	VTUNE	Control Voltage Input. Modulation port bandwidth dependent on drive source impedance.	
4, 5	GND	Package bottom has an exposed metal paddle that must be RF & DC grounded.	
8	RFOUT	RF output (AC coupled).	

Evaluation PCB



List of Materials for Evaluation PCB 104713 ^[1]

Item	Description
J1 - J3	PCB Mount SMA RF Connector
C1	10 μ F Tantalum Capacitor
U1	HMC358MS8G / HMC358MS8GE VCO
PCB [2]	104368 Eval Board

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads and backside ground slug should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.



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Notes: